Andres Mujica

List of Publications by Year
in descending order

63 papers	2,942 citations	257450 24 h-index	161849 54 g-index
64 all docs	64 docs citations	64 times ranked	2148 citing authors

#	Article	IF	Citations
1	Stability of the sc16 polymorph of GaAs. Journal of Physics and Chemistry of Solids, 2021, 159, 110233.	4.0	1
2	Role of rare earth sites and vacancies in the anomalous compression of modulated scheelite tungstates <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow><mml:mi>R</mml:mi><mml:mi>E</mml:mi></mml:mro (<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 692 Td (xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:n	2.4	3
3	Physical Review Materials, 2021, 5, . Orpiment under compression: metavalent bonding at high pressure. Physical Chemistry Chemical Physics, 2020, 22, 3352-3369.	2.8	20
4	Experimental and Theoretical Study of SbPO4 under Compression. Inorganic Chemistry, 2020, 59, 287-307.	4.0	14
5	High-pressure polymorphs of gadolinium orthovanadate: X-ray diffraction, Raman spectroscopy, and ab initio calculations. Physical Review B, 2019, 100, .	3.2	22
6	Thermal evolution of the indentation-induced phases of silicon. Journal of Applied Physics, 2019, 126, .	2.5	8
7	Formation of an r8-Dominant Si Material. Physical Review Letters, 2019, 122, 105701.	7.8	19
8	Metastable States in Pressurized Bulk and Mesoporous Germanium. Journal of Physical Chemistry C, 2018, 122, 10929-10938.	3.1	6
9	Study of the orpiment and anorpiment phases of As2S3 under pressure. Journal of Physics: Conference Series, 2017, 950, 042018.	0.4	4
10	Lattice reduction using a Euclidean algorithm. Acta Crystallographica Section A: Foundations and Advances, 2017, 73, 61-68.	0.1	0
11	New tetrahedral polymorphs of the group-14 elements. Journal of Physics: Conference Series, 2017, 950, 042010.	0.4	0
12	Equation of state and electronic properties of EuVO4: A high-pressure experimental and computational study. Journal of Alloys and Compounds, 2015, 648, 1005-1016.	5.5	17
13	Low-energy tetrahedral polymorphs of carbon, silicon, and germanium. Physical Review B, 2015, 91, .	3.2	90
14	Equation of state of zircon- and scheelite-type dysprosium orthovanadates: a combined experimental and theoretical study. Journal of Physics Condensed Matter, 2014, 26, 025401.	1.8	12
15	Pressure evolution of two polymorphs of Tb2(MoO4)3. High Pressure Research, 2014, 34, 184-190.	1.2	3
16	A combined study of the equation of state of monazite-type lanthanum orthovanadate usingin situhigh-pressure diffraction andab initiocalculations. Acta Crystallographica Section B: Structural Science, Crystal Engineering and Materials, 2014, 70, 533-538.	1.1	16
17	Pressure evolution of the structure of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mtext>La</mml:mtext><mml:mn>2</mml:mn></mml:msub> <mml:mi>(</mml:mi><mml:msub><mml:mtext>WO</mml:mtext><mml:mn>4 xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>with a modulated scheelite-type structure. Physical Review B, 2014, 89, .	3.2	9
18	Structural anomalies related to changes in the conduction mechanisms of Î±-Sm₂(MoO₄)₃. Journal of Physics Condensed Matter, 2013, 25, 035902.	1.8	3

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19	Experimental and theoretical equation of state of DyVO4polymorphs. Acta Crystallographica Section A: Foundations and Advances, 2013, 69, s478-s479.	0.3	0
20	Crystal Chemistry of CdIn₂S₄, MgIn₂S₄, and MnIn₂S₄ Thiospinels under High Pressure. Journal of Physical Chemistry C, 2012, 116, 14078-14087.	3.1	44
21	Theoretical study of pressure-driven phase transitions in HgSe and HgTe. Physical Review B, 2011, 83, .	3.2	12
22	Optical study of the effect of the impurity content on the ferroelectric properties of Er3+ doped SBN glass-ceramic samples. Journal of Applied Physics, 2011, 110, .	2.5	7
23	Electrical transport and anomalous structural behavior of at high temperature. Solid State Communications, 2011, 151, 1654-1658.	1.9	7
24	A combined high-pressure experimental and theoretical study of the electronic band-structure of scheelite-type AWO4 (Aâ€‰=â€‰Ca, Sr, Ba, Pb) compounds. Journal of Applied Physics, 2011, 110, .	2.5	81
25	Soft-phonon instability in zincblende HgSe and HgTe under moderate pressure:Ab initiopseudopotential calculations. Physical Review B, 2009, 80, .	3.2	10
26	Phase transitions in wolframite-type<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>CdWO</mml:mtext></mml:mrow><mml:mn>4</mml:mn></mml: high pressure studied by Raman spectroscopy and density-functional theory. Physical Review B, 2009, 79, .	3.2	64
27	Combined Raman scattering andab initioinvestigation of pressure-induced structural phase transitions in the scintillator<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>ZnWO</mml:mtext></mml:mrow><mml:mn>4</mml:mn></mml:mn></mml Physical Review B, 2008, 78, .	3.2	83
28	Possible non-centrosymmetric structure of vaterite type yttrium orthoborate. Acta Crystallographica Section A: Foundations and Advances, 2008, 64, C467-C468.	0.3	0
29	Different ordered defect scheelite type in RE2(MoO4)3crystal structures. Acta Crystallographica Section A: Foundations and Advances, 2008, 64, C468-C469.	0.3	0
30	Crystal stability and pressure-induced phase transitions in scheelite AWO4 (A = Ca, Sr, Ba, Pb, Eu) binary oxides. I: A review of recentab initio calculations, ADXRD, XANES, and Raman studies. Physica Status Solidi (B): Basic Research, 2007, 244, 325-330.	1.5	31
31	Structural phases of InAs under pressure. Physica Status Solidi (B): Basic Research, 2007, 244, 274-278.	1.5	6
32	Crystal stability and pressure-induced phase transitions in scheelite AWO4 (A = Ca, Sr, Ba, Pb, Eu) binary oxides. II: Towards a systematic understanding. Physica Status Solidi (B): Basic Research, 2007, 244, 295-302.	1.5	34
33	Determination of the high-pressure crystal structure ofBaWO4andPbWO4. Physical Review B, 2006, 73, .	3.2	95
34	Theoretical and experimental study of CaWO4 and SrWO4 under pressure. Journal of Physics and Chemistry of Solids, 2006, 67, 2164-2171.	4.0	24
35	Lattice dynamics study of scheelite tungstates under high pressure I.BaWO4. Physical Review B, 2006, 74, .	3.2	91
36	Lattice dynamics study of scheelite tungstates under high pressure II.PbWO4. Physical Review B, 2006, 74, .	3.2	50

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37	High-pressure structural study of the scheelite tungstatesCaWO4andSrWO4. Physical Review B, 2005, 72, .	3.2	159
38	Theoretical study of ZnS under high pressure. Physica Status Solidi (B): Basic Research, 2003, 235, 452-455.	1.5	8
39	High-pressure phases of group-IV, IIIâ€“V, and IIâ€“VI compounds. Reviews of Modern Physics, 2003, 75, 863-912.	45.6	922
40	High-Pressure Behaviour of Si AND Ge: A Theoretical Study. High Pressure Research, 2002, 22, 455-458.	1.2	1
41	Theoretical Description of High-Pressure Phases of Semiconductors. High Pressure Research, 2002, 22, 421-427.	1.2	71
42	High-pressure phases of germanium. Journal of Physics Condensed Matter, 2001, 13, 35-42.	1.8	6
43	Comparative Study of Novel Structures in Silicon and Germanium. Physica Status Solidi (B): Basic Research, 2001, 223, 379-384.	1.5	19
44	Comparative Study of Novel Structures in Silicon and Germanium. , 2001, 223, 379.		1
45	Theoretical study of the relative stability of structural phases in group-III nitrides at high pressures. Physical Review B, 2000, 62, 16612-16623.	3.2	196
46	High-Pressure Cinnabar-Like Phases in III-V Compounds. Physica Status Solidi (B): Basic Research, 1999, 211, 345-350.	1.5	8
47	AlX (X = As, P, Sb) Compounds under Pressure. Physica Status Solidi (B): Basic Research, 1999, 211, 39-43.	1.5	47
48	High-Pressure Cinnabar-Like Phases in IIIâ€“V Compounds. , 1999, 211, 345.		1
49	Theoretical study of the cinnabar phases in GaAs and GaP. Physical Review B, 1998, 57, 1344-1347.	3.2	38
50	Theoretical study of the high-pressure phase stability of GaP, InP, and InAs. Physical Review B, 1997, 55, 9659-9670.	3.2	101
51	Ground-state properties and high-pressure phase of beryllium chalcogenides BeSe, BeTe, and BeS. Physical Review B, 1996, 54, 11861-11864.	3.2	66
52	Band lineup modification by Ge interlayer deposition at IIâ€“VI/IIIâ€“V semiconductor heterojunctions. Applied Surface Science, 1996, 92, 408-411.	6.1	2
53	Electronic and Structural Properties of BeSe, BeTe, and BeS: Comparison between abâ€initio Theory and Experiments. Physica Status Solidi (B): Basic Research, 1996, 198, 439-446.	1.5	54
54	High Pressure Phases of AlSb from abâ€initio Theory. Physica Status Solidi (B): Basic Research, 1996, 198, 455-459.	1.5	19

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55	High Pressure Stability in IIIâ€“V and IIâ€“VI Binary Compounds and the Cmcm Phase A Theoretical Study. Physica Status Solidi (B): Basic Research, 1996, 198, 461-467.	1.5	17
56	TheCmcmstructure as a stable phase of binary compounds: application to GaAs-II. Journal of Physics Condensed Matter, 1996, 8, L237-L243.	1.8	31
57	First principles calculations of crystal structures and transitions under high pressure. Acta Crystallographica Section A: Foundations and Advances, 1996, 52, C527-C527.	0.3	0
58	First-principles pseudopotential study of the structural phases of silicon. Physical Review B, 1995, 51, 9652-9660.	3.2	105
59	First-principles pseudopotential study of the phase stability of the III-V semiconductors GaAs and AlAs. Physical Review B, 1995, 52, 8881-8892.	3.2	90
60	Interdiffusion effects in the band offset modification by intralayer deposition at semiconductor homojunctions. Physica B: Condensed Matter, 1993, 185, 546-550.	2.7	4
61	First-principles calculations of the structural properties, stability, and band structure of complex tetrahedral phases of germanium: ST12 and BC8. Physical Review B, 1993, 48, 17010-17017.	3.2	61
62	Heterojunction band offsets for polar interfaces: From a thin to a thick covalent intralayer. Physical Review B, 1992, 46, 9641-9647.	3.2	5
63	Selfconsistent tight-binding calculations of band offsets in GaAs/AlxGa1â^'xAs-(110) and GaSb/AlxGa1â^'xSb-(110) heterojunctions theoretical evidence for a new common-anion rule. Solid State Communications, 1992, 81, 961-963.	1.9	6